# TSV630, TSV630A, TSV631, TSV631A

Rail-to-rail input/output 60 µA 880 kHz CMOS operational amplifiers

#### **Features**

- Low offset voltage: 500 µV max (A version)
- Low power consumption: 60 µA typ at 5 V
- Low supply voltage: 1.5 V 5.5 V
- Gain bandwidth product: 880 kHz typ
- Unity gain stability
- Low power shutdown mode: 5 nA typ
- High output current: 63 mA at V<sub>CC</sub> = 5 V
- Low input bias current: 1 pA typ
- Rail-to-rail input and output
- Extended temperature range: -40°C to +125°C

## **Applications**

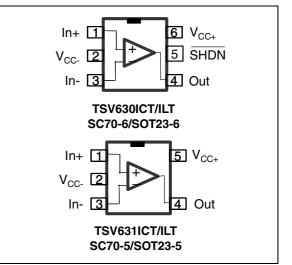
- Battery-powered applications
- Portable devices
- Signal conditioning
- Active filtering
- Medical instrumentation

## Description

The TSV630 and TSV631 devices are single operational amplifiers offering low voltage, low power operation and rail-to-rail input and output.

With a very low input bias current and low offset voltage (500  $\mu$ V maximum for the A version), the TSV630 and TSV631 are ideal for applications that require precision. The devices can operate at power supplies ranging from 1.5 to 5.5 V, and are therefore ideal for battery-powered devices, extending battery life.

These products feature an excellent speed/power consumption ratio, offering a 880 kHz gain bandwidth while consuming only 60  $\mu$ A at a 5-V supply voltage. These op-amps are unity gain stable for capacitive loads up to 100 pF.



Datasheet - production data

The devices are internally adjusted to provide very narrow dispersion of AC and DC parameters, especially power consumption, product gain bandwidth and slew rate.

The TSV630 provides a shutdown function.

Both the TSV630 and TSV631 have a high tolerance to ESD, sustaining 4 kV for the human body model.

Additionally, they are offered in micropackages, SC70-6 and SOT23-6 for the TSV630 and SC70-5 and SOT23-5 for the TSV631. They are guaranteed for industrial temperature ranges from  $-40^{\circ}$  C to  $+125^{\circ}$  C.

All these features combined make the TSV630 and TSV631 ideal for sensor interfaces,batterysupplied and portable applications, as well as active filtering.

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This is information on a product in full production.

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# Absolute maximum ratings and operating conditions

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply voltage <sup>(1)</sup>	6	V
V <sub>id</sub>	Differential input voltage <sup>(2)</sup>	±V <sub>CC</sub>	V
V <sub>in</sub>	Input voltage <sup>(3)</sup>	V <sub>CC-</sub> -0.2 to V <sub>CC+</sub> +0.2	V
l <sub>in</sub>	Input current <sup>(4)</sup>	10	mA
SHDN	Shutdown voltage <sup>(3)</sup>	6	V
T <sub>stg</sub>	Storage temperature	-65 to +150	°C
R <sub>thja</sub>	Thermal resistance junction to ambient <sup>(5)(6)</sup> SC70-5 SOT23-5 SOT23-6 SC70-6	205 250 240 232	°C/W
Тj	Maximum junction temperature	150	°C
ESD	HBM: human body model <sup>(7)</sup> MM: machine model <sup>(8)</sup> CDM: charged device model <sup>(9)</sup>	4 300 1.5	kV V kV
	Latch-up immunity	200	mA

#### Table 1. Absolute maximum ratings (AMR)

1. All voltage values, except differential voltages, are with respect to network ground terminal.

- 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
- 3. V<sub>CC</sub>-V<sub>in</sub> must not exceed 6 V.
- 4. Input current must be limited by a resistor in series with the inputs.
- 5. Short-circuits can cause excessive heating and destructive dissipation.
- 6. R<sub>th</sub> are typical values.
- 7. Human body model: 100 pF discharged through a 1.5 k $\Omega$  resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
- Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω), done for all couples of pin combinations with other pins floating.
- 9. Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to the ground.

Table 2.	Operating conditions
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Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply voltage	1.5 to 5.5	V
V <sub>icm</sub>	Common mode input voltage range	V <sub>CC-</sub> -0.1 to V <sub>CC+</sub> +0.1	V
T <sub>oper</sub>	Operating free air temperature range	-40 to +125	°C



# 2 Electrical characteristics

Table 3.Electrical characteristics at  $V_{CC+} = +1.8$  V with  $V_{CC-} = 0$  V,  $V_{icm} = V_{CC}/2$ ,  $T_{amb} = 25^{\circ}$  Cand  $R_L$  connected to  $V_{CC}/2$  (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perfo	rmance					
		TSV630-TSV631 TSV630A-TSV631A			3 0.5	mV
V <sub>io</sub>	Offset voltage	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub> TSV630-TSV631 TSV630A-TSV631A			4.5 2	mV
DVio	Input offset voltage drift			2		μV/°C
	Input offset current			1	10 <sup>(1)</sup>	n۸
I <sub>io</sub>	$(V_{out} = V_{CC}/2)$	$T_{min} < T_{op} < T_{max}$		1	100	рА
L.	Input bias current			1	10 <sup>(1)</sup>	pА
l <sub>ib</sub>	$(V_{out} = V_{CC}/2)$	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>		1	100	рл
CMR	Common mode rejection ratio	0 V to 1.8 V, $V_{out} = 0.9 V$	53	74		dB
OWIT	20 log ( $\Delta V_{ic}/\Delta V_{io}$ )	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	51			άĐ
A <sub>vd</sub>	Large signal voltage gain	$\rm R_L{=}$ 10 kΩ, $\rm V_{out}{=}$ 0.5 V to 1.3 V	85	95		- dB
۸vd	Large signal voltage gain	$T_{min} < T_{op} < T_{max}$	80			
V <sub>OH</sub>	High level output voltage	$R_L = 10 \ k\Omega$	35	5		mV
•OH	ngin level output voltage	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	50			
V <sub>OL</sub>	Low level output voltage	$R_L = 10 \ k\Omega$		4	35	mV
۰OL		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			50	
		V <sub>o</sub> = 1.8 V	6	12		mA
I <sub>out</sub>	lsink	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	4			
out		$V_0 = 0 V$	6	10		mA
	Isource	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	4			11// (
I <sub>CC</sub>	Supply current	No load, $V_{out} = V_{CC}/2$	40	50	60	μA
	SHDN = V <sub>CC+</sub>	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			62	P// 1
AC perfo	rmance					
GBP	Gain bandwidth product	$R_L = 2 \text{ k}\Omega, C_L = 100 \text{ pF}, f = 100 \text{ kHz}$	700	790		kHz
φm	Phase margin	$R_{L} = 2 k\Omega, C_{L} = 100 pF$		48		Degrees
G <sub>m</sub>	Gain margin	$R_L = 2 k\Omega$ , $C_L = 100 pF$		11		dB
SR	Slew rate	$R_L = 2 k\Omega$ , $C_L = 100 pF$ , $Av = 1$	0.2	0.27		V/µs
e <sub>n</sub>	Equivalent input noise voltage	f = 1 kHz f = 10 kHz		67 53		<u>nV</u> √Hz

1. Guaranteed by design.



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit			
DC perfo	DC performance								
	Supply current in shutdown	SHDN = V <sub>CC-</sub>		2.5	50	nA			
I <sub>CC</sub>	mode	$T_{min} < T_{op} < 85^{\circ} C$			200	nA			
	(all operators)	T <sub>min</sub> < T <sub>op</sub> < 125° C			1.5	μA			
t <sub>on</sub>	Amplifier turn-on time	$R_L = 2 \text{ k}$ , Vout = $V_{CC} + 0.2 \text{ to}$ $V_{CC} - 0.2$		300		ns			
t <sub>off</sub>	Amplifier turn-off time	$R_L = 2 \text{ k}$ , Vout = $V_{CC-} + 0.2 \text{ to}$ $V_{CC+} - 0.2$		20		ns			
V <sub>IH</sub>	SHDN logic high		1.3			V			
V <sub>IL</sub>	SHDN logic low				0.5	V			
I <sub>IH</sub>	SHDN current high	$\overline{\text{SHDN}} = V_{\text{CC+}}$		10		pА			
Ι <sub>ΙL</sub>	SHDN current low	SHDN = V <sub>CC-</sub>		10		pА			
I	Output leakage in shutdown	SHDN = V <sub>CC-</sub>		50		pА			
IOLeak	mode	T <sub>min</sub> < T <sub>op</sub> < 125° C		1		nA			

# Table 4.Shutdown characteristics V<sub>CC</sub> = 1.8 V



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perfor	mance					
		TSV630-TSV631 TSV630A-TSV631A			3 0.5	mV
V <sub>io</sub>	V <sub>io</sub> Offset voltage	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub> TSV630-TSV631 TSV630A-TSV631A			4.5 2	mV
DVio	Input offset voltage drift			2		μV/°C
	Input offect ourrent			1	10 <sup>(1)</sup>	-
I <sub>io</sub>	Input offset current	$T_{min} < T_{op} < T_{max}$		1	100	рА
L.	Input bias current			1	10 <sup>(1)</sup>	n۸
l <sub>ib</sub>	input bias current	$T_{min} < T_{op} < T_{max}$		1	100	рА
CMR	Common mode rejection	0 V to 3.3 V, $V_{out} = 1.75 V$	57	79		dB
Civin	ratio 20 log ( $\Delta V_{ic}/\Delta V_{io}$ )	$T_{min} < T_{op} < T_{max}$	53			
A <sub>vd</sub>	Large signal voltage gain	$R_L$ = 10 k $\Omega$ V $_{out}$ = 0.5 V to 2.8 V	88	98		dB
Avd	Large signal voltage gain	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	83			uD
V <sub>OH</sub>	High level output voltage	$R_L = 10 \ k\Omega$	35	6		mV
VОН	Tightievel output voltage	$T_{min.} < T_{op} < T_{max}$	50			111 V
V <sub>OL</sub>	Low level output voltage	$R_L = 10 \ k\Omega$		7	35	mV
♥ OL	Low level output voltage	$T_{min} < T_{op} < T_{max}$			50	111 V
	1	V <sub>o</sub> = 3.3 V	30	45		mA
	l <sub>sink</sub>	$T_{min} < T_{op} < T_{max}$	25	42		
I <sub>out</sub>		$V_o = 0 V$	30	38		mA
	Isource	$T_{min} < T_{op} < T_{max}$	25			
laa	Supply current	No load, $V_{out} = 1.75 \text{ V}$	43	55	64	μA
ICC	SHDN = V <sub>CC+</sub>	$T_{min} < T_{op} < T_{max}$			66	μΑ
AC perfor	mance					
GBP	Gain bandwidth product	$R_L = 2 \text{ k}\Omega, C_L = 100 \text{ pF}, \text{ f} = 100 \text{ kHz}$	710	860		kHz
φm	Phase margin	$R_L = 2 k\Omega$ , $C_L = 100 pF$		50		Degrees
G <sub>m</sub>	Gain margin	$R_L = 2 k\Omega$ , $C_L = 100 pF$		11		dB
SR	Slew rate	$R_L = 2 k\Omega, C_L = 100 \text{ pF}, \text{ Av} = 1$	0.22	0.29		V/µs
e <sub>n</sub>	Equivalent input noise voltage	f = 1 kHz f = 10 kHz		64 51		<u>nV</u> √Hz

# Table 5.Electrical characteristics at $V_{CC+} = +3.3 \text{ V}$ , $V_{CC-} = 0 \text{ V}$ , $V_{icm} = V_{CC}/2$ , $T_{amb} = 25^{\circ} \text{ C}$ , $R_L$ connected to $V_{CC}/2$ (unless otherwise specified)

1. Guaranteed by design.



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perfor	mance		•		•	
		TSV630-TSV631 TSV630A-TSV631A			3 0.5	mV
V <sub>io</sub>	Offset voltage	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub> TSV630-TSV631 TSV630A-TSV631A			4.5 2	mV
DVio	Input offset voltage drift			2		μV/°C
1	Input offset current			1	10 <sup>(1)</sup>	-
I <sub>io</sub>	$(V_{out} = V_{CC}/2)$	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>		1	100	рА
I	Input bias current			1	10 <sup>(1)</sup>	-
I <sub>ib</sub>	$(V_{out} = V_{CC}/2)$	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>		1	100	рА
CMR	Common mode rejection ratio	0 V to 5 V, $V_{out} = 2.5 V$	60	80		dD
CIVIR	20 log ( $\Delta V_{ic}/\Delta V_{io}$ )	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	55			dB
	Supply voltage rejection ratio	V <sub>CC</sub> = 1.8 to 5 V	75	102		
SVR	20 log ( $\Delta V_{CC}/\Delta V_{io}$ )	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>				dB
٨	Large signal voltage gain	$R_L$ = 10 k $\Omega$ , $V_{out}$ = 0.5 V to 4.5 V	89	98		dB
A <sub>vd</sub>		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	84			uв
V		$R_L = 10 \text{ k}\Omega$	35	7		m)/
V <sub>OH</sub>	High level output voltage	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	50			mV
V		$R_L = 10 \text{ k}\Omega$		6	35	mV
V <sub>OL</sub>	Low level output voltage	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			50	
		$V_0 = 5 V$	40	69		mA
	lsink	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	35	65		
l <sub>out</sub>	1	$V_0 = 0 V$	40	74		mA
	Isource	$T_{min} < T_{op} < T_{max}$	36	68		
	Supply current	No load, V <sub>out</sub> =V <sub>CC</sub> /2	50	60	69	
I <sub>CC</sub>	$\overline{SHDN} = V_{CC+}$	T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			72	μA
AC perfor	mance	•				
GBP	Gain bandwidth product	$ \begin{array}{l} R_{L} = 2 \; k \Omega , \; C_{L} = 100 \; pF , \\ f = 100 \; kHz \end{array} $	730	880		kHz
Fu	Unity gain frequency	$R_L = 2 k\Omega, C_L = 100 pF,$		830		kHz
φm	Phase margin	$R_{L} = 2 k\Omega, C_{L} = 100 pF$		50		Degrees
G <sub>m</sub>	Gain margin	$R_{L} = 2 k\Omega, C_{L} = 100 pF$		12		dB
SR	Slew rate	$R_L = 2 k\Omega$ , $C_L = 100 pF$ , $Av = 1$	0.25	0.34		V/µs

# Table 6.Electrical characteristics at $V_{CC+} = +5 V$ with $V_{CC-} = 0 V$ , $V_{icm} = V_{CC}/2$ , $T_{amb} = 25^{\circ} C$ and<br/> $R_L$ connected to $V_{CC}/2$ (unless otherwise specified)



%

$R_L$ connected to $V_{CC}/2$ (unless otherwise specified) (continued)							
SymbolParameterConditionsMin.Typ.Max.							
	e <sub>n</sub> Equivalent input noise voltage	f = 1 kHz		60		nV	
e <sub>n</sub>		f = 10 kHz		47		<u>nV</u> √Hz	

Table 6.	Electrical characteristics at $V_{CC+}$ = +5 V with $V_{CC-}$ = 0 V, $V_{icm}$ = $V_{CC}/2$ , $T_{amb}$ = 25° C and
	R <sub>L</sub> connected to V <sub>CC</sub> /2 (unless otherwise specified) (continued)

				i
e <sub>n</sub>	Equivalent input noise voltage	f = 1 kHz f = 10 kHz	60 47	
THD+e <sub>n</sub>	Total harmonic distortion	f = 1 kHz, $A_V$ = 1, $R_L$ = 100 kΩ, V <sub>icm</sub> = V <sub>CC</sub> /2, Vout = 2 V <sub>PP</sub>	0.0017	

1. Guaranteed by design.

Table 7.	Shutdown	characteristics	$V_{CC} = 5 V$
Table 7.	Shutdown	characteristics	$V_{CC} = 5 V$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perform	nance					
		SHDN = V <sub>CC-</sub>		5	50	nA
I <sub>CC</sub>	Supply current in shutdown mode (all operators)	T <sub>min</sub> < T <sub>op</sub> < 85° C			200	nA
		T <sub>min</sub> < T <sub>op</sub> < 125° C			1.5	μΑ
t <sub>on</sub>	Amplifier turn-on time	$R_L = 2 \text{ k}$ , Vout = $V_{CC-} + 0.2 \text{ to}$ $V_{CC+} - 0.2$		300		ns
t <sub>off</sub>	Amplifier turn-off time	$R_L = 2 \text{ k}$ , Vout = $V_{CC-} + 0.2 \text{ to}$ $V_{CC+} - 0.2$		30		ns
V <sub>IH</sub>	SHDN logic high		4.5			V
V <sub>IL</sub>	SHDN logic low				0.5	V
I <sub>IH</sub>	SHDN current high	$\overline{\text{SHDN}} = V_{\text{CC+}}$		10		pА
IIL	SHDN current low	$\overline{\text{SHDN}} = V_{\text{CC}}$		10		pА
1.	Output leakage in shutdown	$\overline{SHDN} = V_{CC}$		50		pА
IOLeak	mode	T <sub>min</sub> < T <sub>op</sub> < 125° C		1		nA



Figure 1. Supply current vs. supply voltage at  $V_{icm} = V_{CC}/2$ 



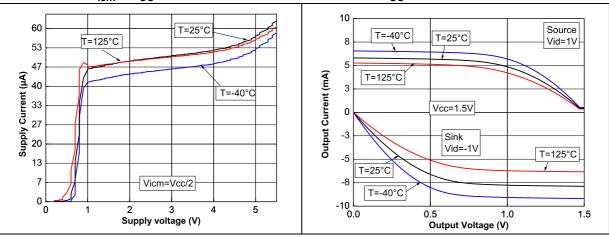
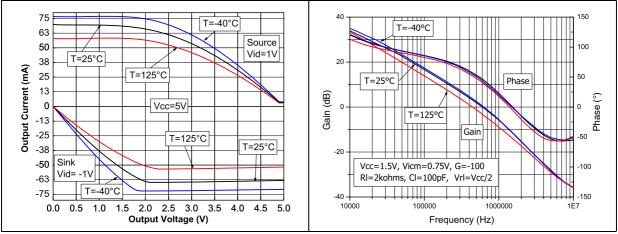
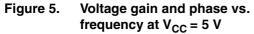


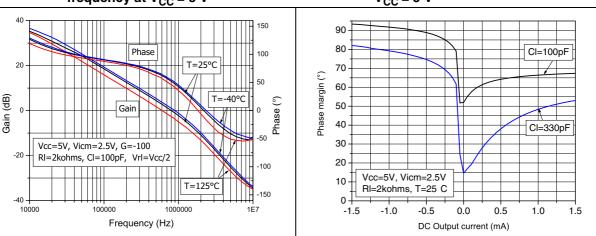
Figure 3. Output current vs. output voltage at Figure 4.  $V_{CC} = 5 V$ 

Voltage gain and phase vs. frequency at  $V_{CC}$  = 1.5 V



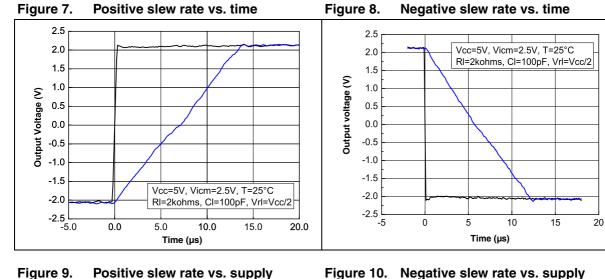


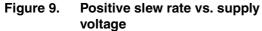




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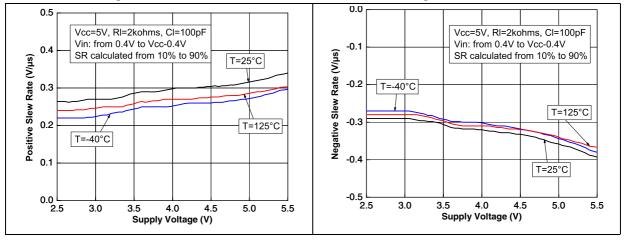
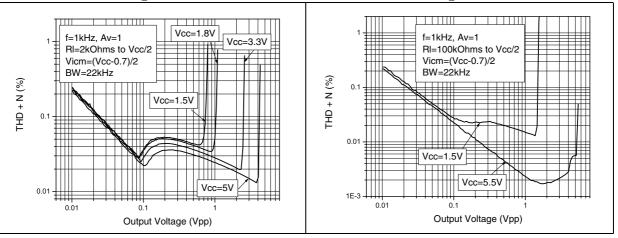


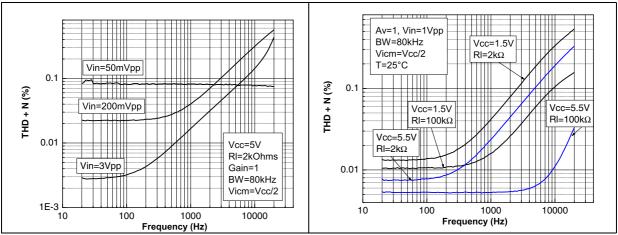
Figure 11. Distortion + noise vs. output voltage ( $R_L = 2 k\Omega$ )

Figure 12. Distortion + noise vs. output voltage ( $R_1 = 100 \text{ k}\Omega$ )

voltage



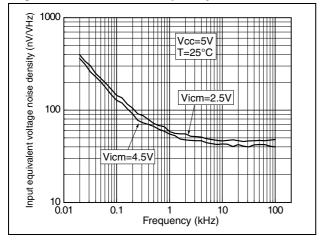




#### Figure 13. Distortion + noise vs. frequency

#### Figure 14. Distortion + noise vs. frequency

Figure 15. Noise vs. frequency



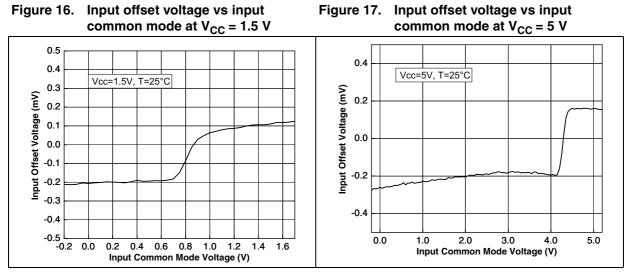
# **3** Application information

### 3.1 Operating voltages

The TSV630 and TSV631 can operate from 1.5 to 5.5 V. Their parameters are fully specified for 1.8-, 3.3- and 5-V power supplies. However, the parameters are very stable in the full V<sub>CC</sub> range and several characterization curves show the TSV63x characteristics at 1.5 V. Additionally, the main specifications are guaranteed in extended temperature ranges from - 40° C to +125° C.

## 3.2 Rail-to-rail input

The TSV630 and TSV631 are built with two complementary PMOS and NMOS input differential pairs. The devices have a rail-to-rail input, and the input common mode range is extended from  $V_{CC-}$  -0.1 V to  $V_{CC+}$  +0.1 V. The transition between the two pairs appears at  $V_{CC+}$  -0.7 V. In the transition region, the performance of CMRR, PSRR,  $V_{io}$  and THD is slightly degraded (as shown in *Figure 16* and *Figure 17* for  $V_{io}$  vs.  $V_{icm}$ ).



The device is guaranteed without phase reversal.

## 3.3 Rail-to-rail output

The operational amplifiers' output levels can go close to the rails: 35 mV maximum above and below the rail when connected to a 10 k $\Omega$  resistive load to V<sub>CC</sub>/2.

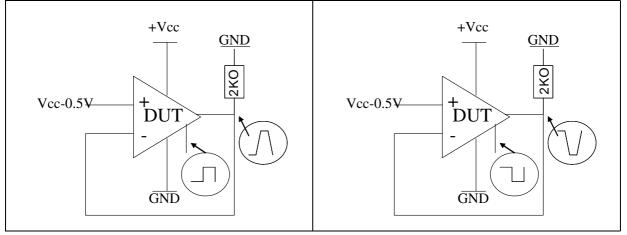


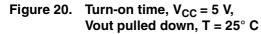
## 3.4 Shutdown function (TSV630)

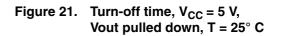
The operational amplifier is enabled when the  $\overline{SHDN}$  pin is pulled high. To disable the amplifier, the  $\overline{SHDN}$  must be pulled down to  $V_{CC-}$ . When in shutdown mode, the amplifier output is in a high impedance state. The  $\overline{SHDN}$  pin must never be left floating, but tied to  $V_{CC+}$  or  $V_{CC-}$ .

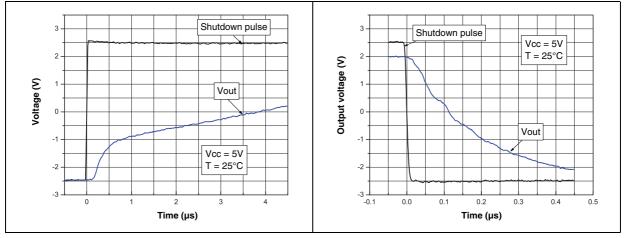
The turn-on and turn-off time are calculated for an output variation of  $\pm 200 \text{ mV}$  (*Figure 18* and *Figure 19* show the test configurations).

# Figure 18.Test configuration for turn-on timeFigure 19.Test configuration for turn-off time<br/>(Vout pulled down)(Vout pulled down)(Vout pulled down)











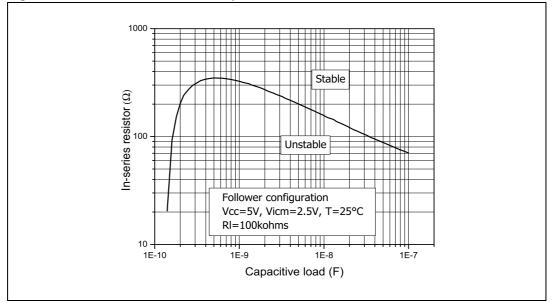
### 3.5 Optimization of DC and AC parameters

These devices use an innovative approach to reduce the spread of the main DC and AC parameters. An internal adjustment achieves a very narrow spread of the current consumption (60  $\mu$ A typical, min/max at ±17 %). Parameters linked to the current consumption value, such as GBP, SR and AVd, benefit from this narrow dispersion. All parts present a similar speed and the same behavior in terms of stability. In addition, the minimum values of GBP and SR are guaranteed (GBP = 730 kHz minimum and SR = 0.25 V/µs minimum).

### 3.6 Driving resistive and capacitive loads

These products are micro-power, low-voltage operational amplifiers optimized to drive rather large resistive loads, above 2 k $\Omega$  For lower resistive loads, the THD level may significantly increase.

In a *follower* configuration, these operational amplifiers can drive capacitive loads up to 100 pF with no oscillations. When driving larger capacitive loads, adding an in-series resistor at the output can improve the stability of the devices (see *Figure 22* for recommended in-series resistor values). Once the in-series resistor value has been selected, the stability of the circuit should be tested on bench and simulated with the simulation model.





### 3.7 PCB layouts

For correct operation, it is advised to add 10 nF decoupling capacitors as close as possible to the power supply pins.

### 3.8 Macromodel

An accurate macromodel of the TSV630 and TSV631 is available on STMicroelectronics' web site at www.st.com. This model is a trade-off between accuracy and complexity (that is, time simulation) of the TSV63x operational amplifiers. It emulates the nominal performances of a typical device within the specified operating conditions mentioned in the datasheet. It also helps to validate a design approach and to select the right operational amplifier, *but it does not replace on-board measurements*.

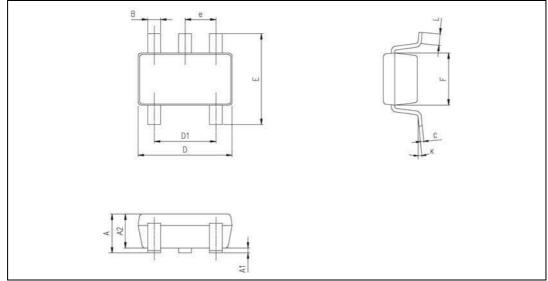


# 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: www.st.com. ECOPACK<sup>®</sup> is an ST trademark.



# 4.1 SOT23-5 package mechanical data



#### Figure 23. SOT23-5L package mechanical drawing

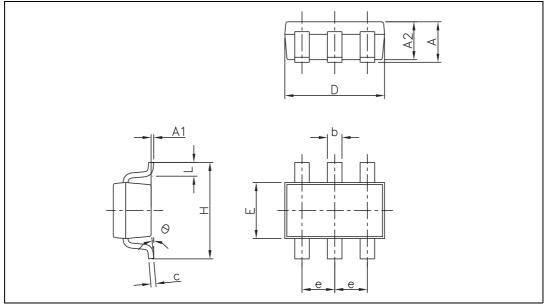
Table 8.SOT23-5L package mechanical data
--

	Dimensions					
Ref.		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	0.90	1.20	1.45	0.035	0.047	0.057
A1			0.15			0.006
A2	0.90	1.05	1.30	0.035	0.041	0.051
В	0.35	0.40	0.50	0.013	0.015	0.019
С	0.09	0.15	0.20	0.003	0.006	0.008
D	2.80	2.90	3.00	0.110	0.114	0.118
D1		1.90			0.075	
е		0.95			0.037	
E	2.60	2.80	3.00	0.102	0.110	0.118
F	1.50	1.60	1.75	0.059	0.063	0.069
L	0.10	0.35	0.60	0.004	0.013	0.023
К	0 degrees		10 degrees			



# 4.2 SOT23-6 package mechanical data

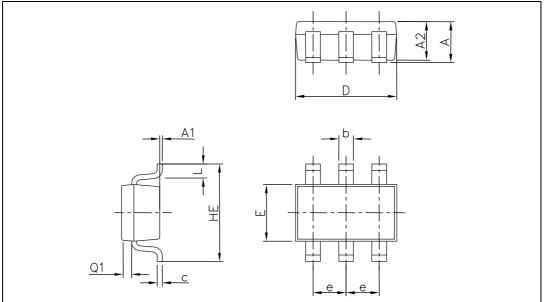
#### Figure 24. SOT23-6L package mechanical drawing



#### Table 9. SOT23-6L package mechanical data

	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	0.90		1.45	0.035		0.057	
A1			0.10			0.004	
A2	0.90		1.30	0.035		0.051	
b	0.35		0.50	0.013		0.019	
С	0.09		0.20	0.003		0.008	
D	2.80		3.05	0.110		0.120	
Е	1.50		1.75	0.060		0.069	
е		0.95			0.037		
Н	2.60		3.00	0.102		0.118	
L	0.10		0.60	0.004		0.024	
o	0		10°				

# 4.3 SC70-6 (or SOT323-6) package mechanical data

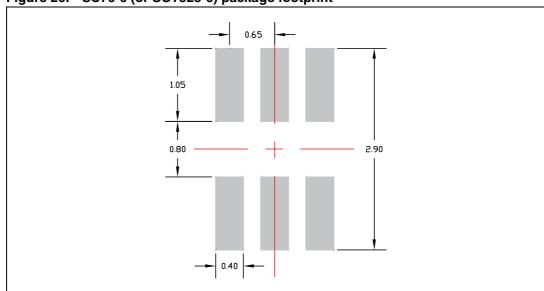


#### Figure 25. SC70-6 (or SOT323-6) package mechanical drawing

#### Table 10. SC70-6 (or SOT323-6) package mechanical data

	Dimensions					
Ref		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	0.80		1.10	0.031		0.043
A1			0.10			0.004
A2	0.80		1.00	0.031		0.039
b	0.15		0.30	0.006		0.012
с	0.10		0.18	0.004		0.007
D	1.80		2.20	0.071		0.086
E	1.15		1.35	0.045		0.053
е		0.65			0.026	
HE	1.80		2.40	0.071		0.094
L	0.10		0.40	0.004		0.016
Q1	0.10		0.40	0.004		0.016

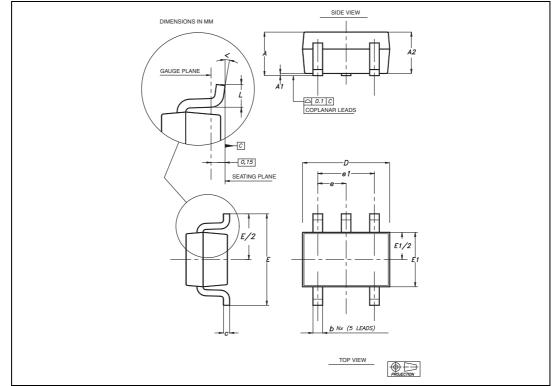




#### Figure 26. SC70-6 (or SOT323-6) package footprint



# 4.4 SC70-5 (or SOT323-5) package mechanical data



#### Figure 27. SC70-5 (or SOT323-5) package mechanical drawing

Table 11.	SC70-5 (or SOT323-5) package mechanical data

	Dimensions						
Ref		Millimeters			Inches		
	Min	Тур	Мах	Min	Тур	Max	
А	0.80		1.10	0.315		0.043	
A1			0.10			0.004	
A2	0.80	0.90	1.00	0.315	0.035	0.039	
b	0.15		0.30	0.006		0.012	
с	0.10		0.22	0.004		0.009	
D	1.80	2.00	2.20	0.071	0.079	0.087	
E	1.80	2.10	2.40	0.071	0.083	0.094	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65			0.025		
e1		1.30			0.051		
L	0.26	0.36	0.46	0.010	0.014	0.018	
<	0°		8°				



# 5 Ordering information

#### Table 12. Order codes

Part number	Temperature range	Package	Packing	Marking
TSV630ILT	-40°C to +125°C	SOT23-6	Tape & reel	K108
TSV630ICT	-40°C to +125°C	SC70-6	Tape & reel	K18
TSV631ILT	-40°C to +125°C	SOT23-5	Tape & reel	K109
TSV631ICT	-40°C to +125°C	SC70-5	Tape & reel	K19
TSV630AILT	-40°C to +125°C	SOT23-6	Tape & reel	K141
TSV630AICT	-40°C to +125°C	SC70-6	Tape & reel	K41
TSV631AILT	-40°C to +125°C	SOT23-5	Tape & reel	K142
TSV631AICT	-40°C to +125°C	SC70-5	Tape & reel	K42



# 6 Revision history

Table 13.	Document revision history
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Date	Revision	Changes
19-Dec-2008	1	Initial release.
17-Aug-2009	2	Added root part numbers TSV630A and TSV631A on cover page.
13-Aug-2012	3	<ul> <li>Corrected the "Equivalent input noise voltage" values in <i>Table 3, 5</i> and <i>6</i>.</li> <li>Updated <i>Figure 15: Noise vs. frequency</i>.</li> </ul>



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